ABSTRACT

METHOD AND APPARATUS FOR THROUGH-SILICON VIAS REVEAL

The present invention provides a method and an apparatus for TSVs reveal. The method includes steps of: providing a Si substrate having a plurality of TSVs formed inside the Si substrate; rotating the Si substrate and spraying a first etchant onto the backside of the Si substrate to etch the backside of the Si substrate, and stopping etching before the TSVs being exposed to the backside of the Si substrate; and rotating the Si substrate and spraying a second etchant onto the backside of the Si substrate to etch the backside of the Si substrate until the TSVs being exposed to the backside of the Si substrate, wherein reversing the rotation direction of the Si substrate at fixed intervals during spraying the second etchant onto the backside of the Si substrate.

FIG.1